



eltic-Plus⁺

Smart Connected World



Celtic-Plus Event
28-29 April 2016, Stockholm

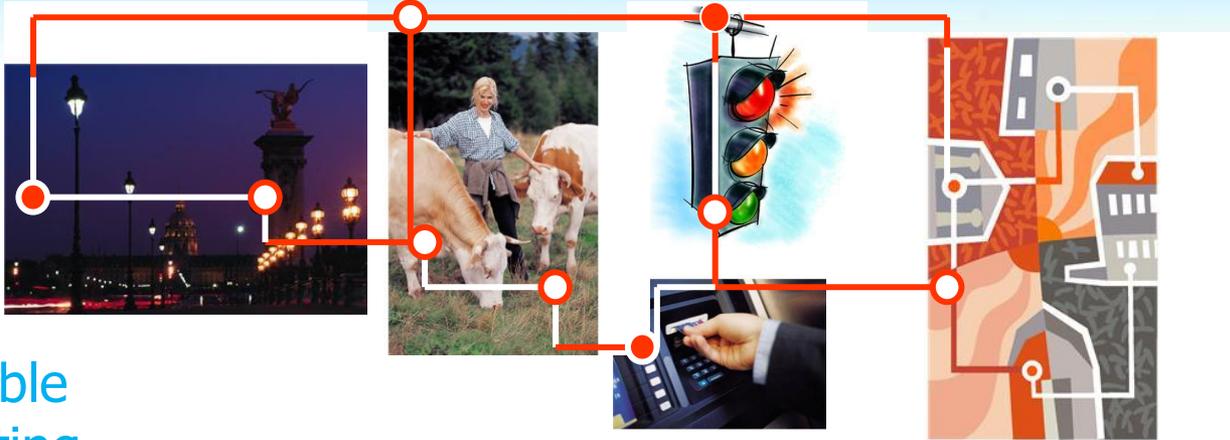
**The Smart Sensor
& Semiconductor NVM Switch.**



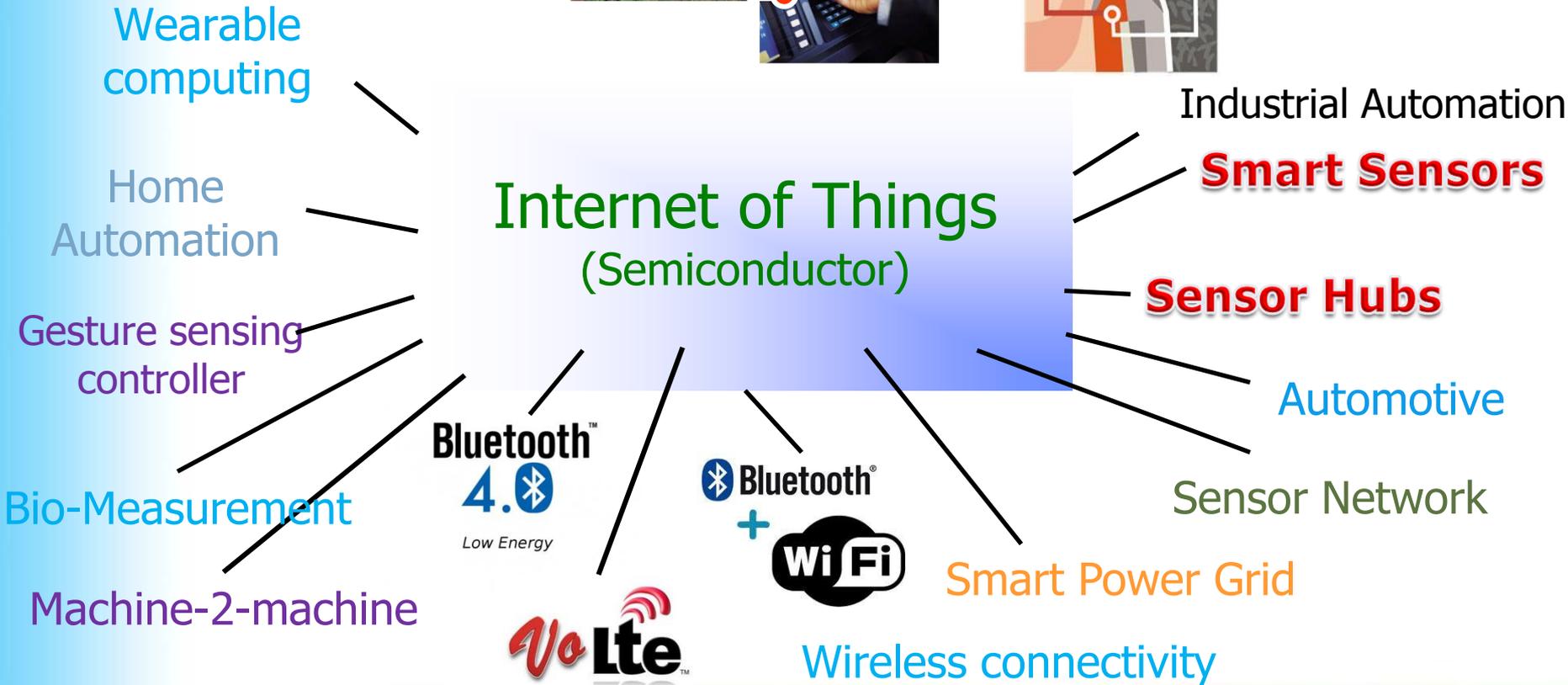
Prof. Yunsik Lee
www.unist.ac.kr



What makes IoT success?



Internet of Things (Semiconductor)



World Leading University

- ❑ Open : 2009.03.
- ❑ Korean Government Funded
- ❑ 10 Schools, 23 Tracks,
- ❑ 400 Faculty, 5,000 Students
- ❑ US152M\$ Budget for Schools



No.	Name	Citation Per Publication	Outputs in the top Percentiles	Field Weighted Citation Impact
1	Caltech	17.7	38.6	2.51
2	Harvard	15.2	33.7	2.43
3	Stanford	14	30.9	2.5
4	MIT	14	30.1	2.44
5	UC-Berkeley	13.9	29.2	2.49
6	Univ. of Chicago	13.8	29.6	2.33
7	Duke Univ.	13.3	28.7	2.23
8	Johns Hopkins Univ.	13.2	29.9	2.19
9	Yale Univ.	12.9	30.7	2.1
10	Univ. of Oxford	12.5	28.6	2.26
11	Univ. of Cambridge	12.4	28.6	2.13
12	Univ. of Pennsylvania	12.3	28	2.2
13	Princeton Univ.	12.2	28.2	2.27
14	Columbia Univ.	12.1	27.8	2.18
15	Imperial College London	11.9	28.6	2.16
16	UNIST	11.8(16위)	31(3위)	2.17(13위)
17	Cornell Univ.	11.7	26.7	2.11
18
29	싱가포르국립대	9	22.5	1.78
30	홍콩대	7.9	20.2	1.61



Wifi

Almost all RF/internet protocols need 32bit MCU to run!

Processor Unit:
Microprocessor,
Microcontroller,
DSP, FPU...

Data processing
Flow control
IO control
Basic Data analysis
Data encryption



Bluetooth 4.0



Wireless Connectivity Unit:
WiFi, GPS, BT,
Proprietary RF,
3G/4G, VoLTE,
Zigbee,...

IoT Device

I/O Unit:
Sensors, I/Os,
Displays...

thermal
pressure
G-sensor
....

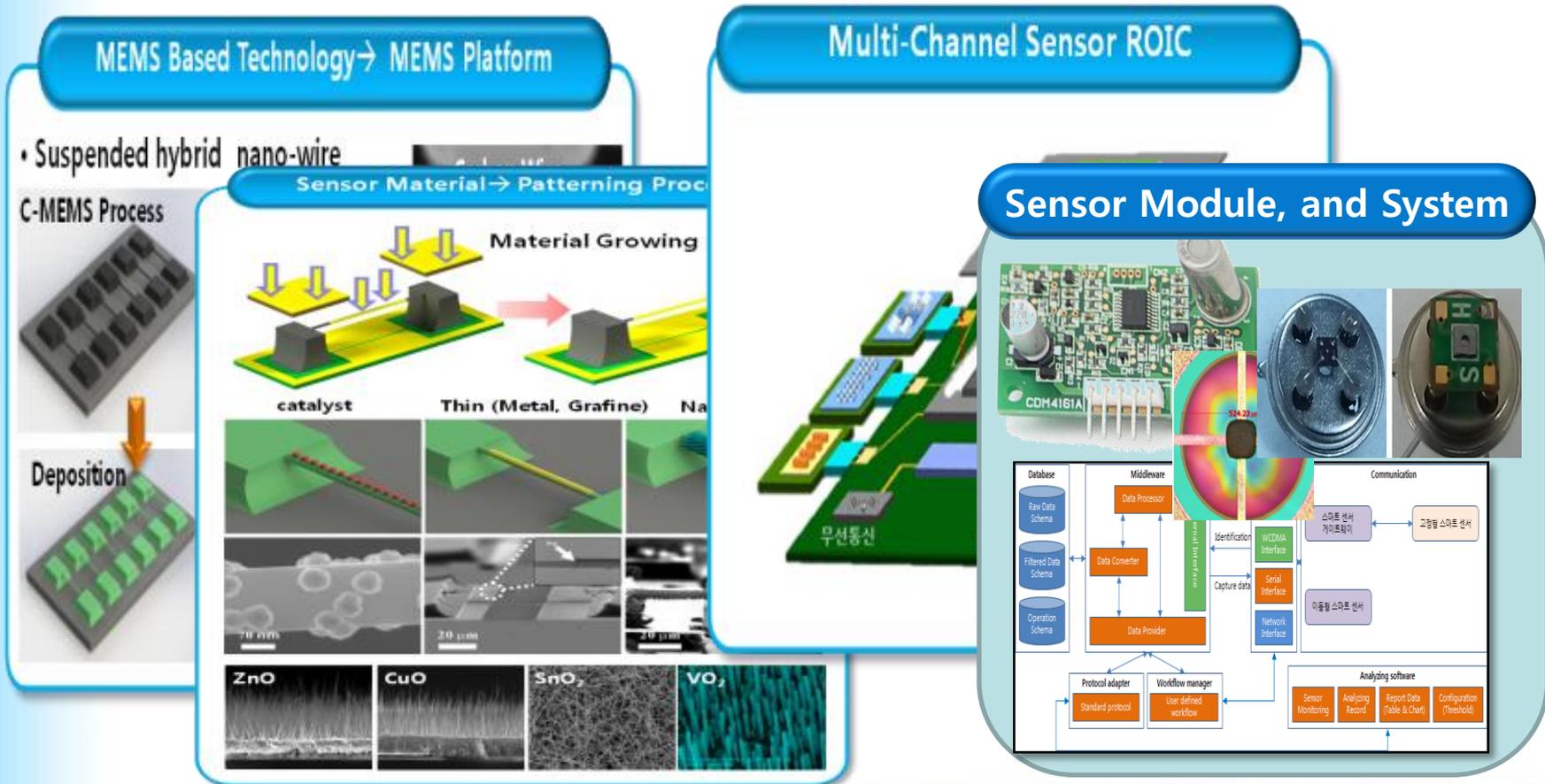


Lte



Proposal Introduction / 1. sensor

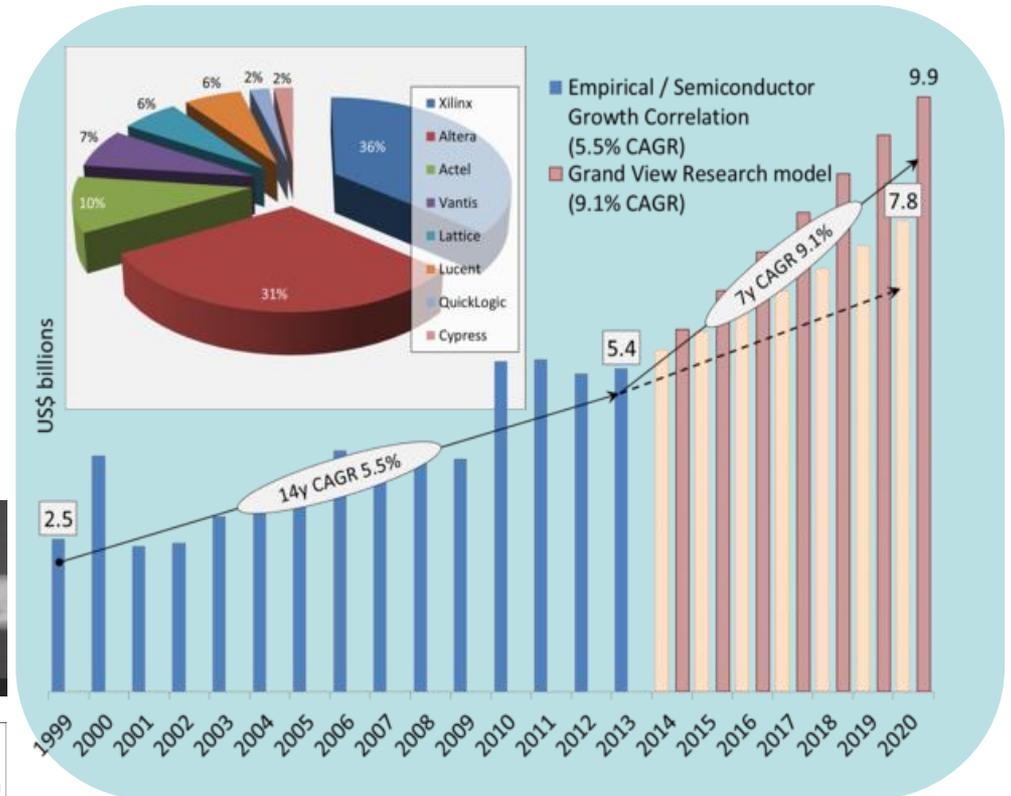
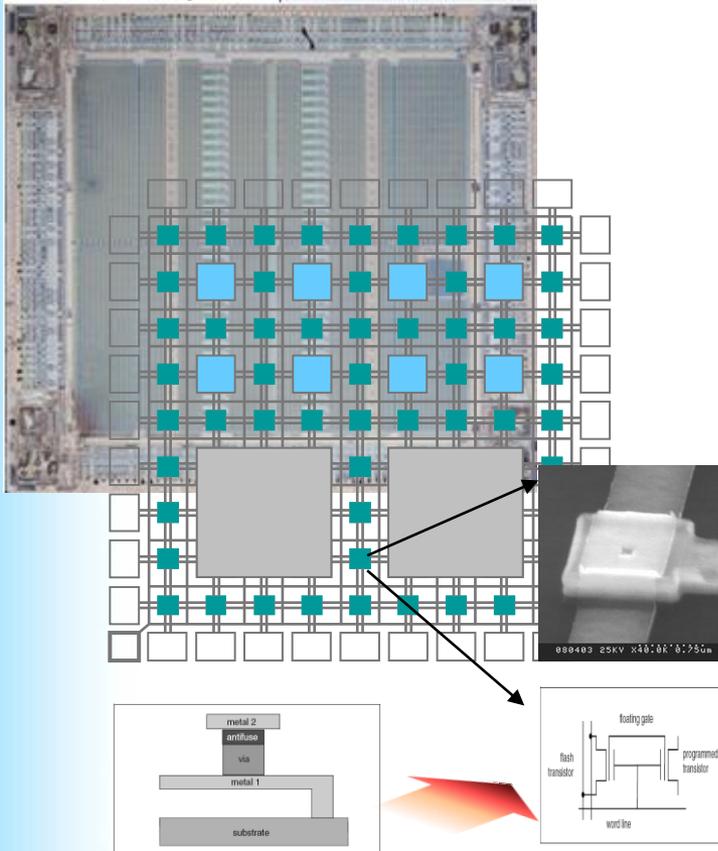
- World class CMOS based smart gas sensor, prototype available at 2017.
- Joint R&D development and business.



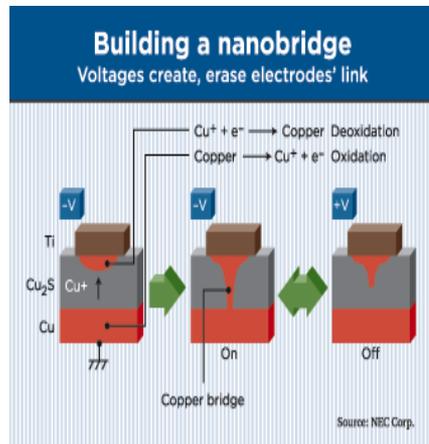
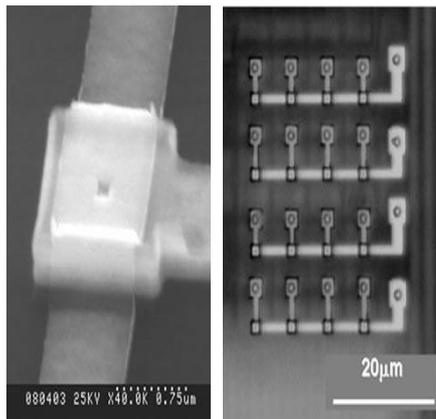
Proposal Introduction /2. Conf. Device

- ☞ Configurable device(FPGA) is ideal for future!
- ☞ SW driven semiconductor/ US6B\$ market

FPGA(Configurable Device)



- 👉 R&D on the device switch(NVM)
- 👉 Seeking partner to joint R&D!

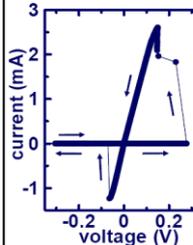


- Function: Nonvolatile, reprogrammable, solid-electrolyte switch
- **Performance Target** (SRAM switch)
 - 1/30 area ($4F^2$ vs. $120F^2$)
 - 1/40 turn-on resistance (50Ω vs. $2K\Omega$)

● Current Statue

- ① 1st Gen.
 - Based on Cu_2S
 - 1 month data retention time
- ② 2nd Gen.
 - Based on Ta_2O_5
 - Improved turn-on voltage
 - 10 year retention time
 - Compatible with standard logic process

Features of Cu_2S solid-electrolyte switch



Meet the demand for programmable logic?

Parameter	Cu_2S NanoBridge
ON resistance	OK ($<100\Omega$)
Switch size	OK ($4F^2$)
Switching speed	OK ($<10\mu\text{sec}$)
Cycling endurance	OK (10^3-10^5)
Turn-on voltage	NG ($\sim 0.2V$)
Retention	NG ($<3\text{month}$)
Process compatible	NG
Switching current	NG ($>3mA$)

Breakthrough in Material (Ta_2O_5)

Parameter Name	Cu_2S switch ¹⁾	Ta_2O_5 switch
ON resistance	OK ($<100\Omega$)	OK ($<100\Omega$)
Switch size	OK ($4F^2$)	OK ($4-8F^2$)
Switching speed	OK ($<10\mu\text{sec}$)	OK ($<100\mu\text{sec}$)
Cycling endurance	OK (10^3-10^5)	OK (10^4)
Switching voltage	NG ($\sim 0.2V$)	OK ($>1V$)
ON-state duration	NG ($<3\text{month}$)	OK ($>10\text{years}$)
Turn-off current	NG ($>3mA$)	Allowable ($\sim 5mA$)
Process Compatibility	NG	OK



Partners(sensor, FPGA, etc.)



sensor

FPGA

R&D Partner



For more information and for interest to participate please contact:



Prof. Yunsik Lee/UNIST

Email: leeys@unist.ac.kr

Phone: (+82)52-217-2112

Addr. :

50 UNIST-gil, Eonyang-eup, Ulju-gun,
Ulsan City, Korea/ zip 44919

web: www.unist.ac.kr